

4V Drive Nch+Nch MOSFET

SH8K5

Structure

Silicon N-channel MOSFET

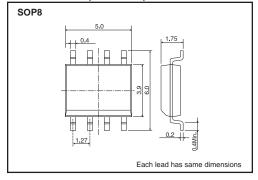
Features

- 1) Low on-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small surface Mount Package (SOP8).

Application

Power switching, DC / DC converter.

•Dimensions (Unit : mm)



Packaging specifications

	Package	Taping
Туре	Code	ТВ
	Basic ordering unit (pieces)	2500
SH8K5		0

•Absolute maximum ratings (Ta=25°C)

< It is the same ratings for the Tr1 and Tr2.>

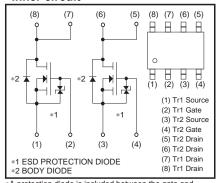
Parameter		Symbol	Limits	Unit
Drain-source voltage		Vdss	30	V
Gate-source voltage		Vgss	±20	V
Dualia aurorant	Continuous	lo	±3.5	А
Drain current	Pulsed	IDP *1	±14	А
Source current	Continuous	ls	1.6	Α
(Body diode)	Pulsed	Isp *1	6.4	А
Total power dissipation		Po *2	2	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

*1 Pw≤10µs, Duty cycle≤1%
*2 MOUNTED ON A CERAMIC BOARD.

•Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth (ch-a)*	62.5	°C / W
*MOUNTED ON A CERAMIC BOARD.			

Inner circuit



*A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

•Electrical characteristics (Ta=25°C) <It is the same characteristics for the Tr1 and Tr2.>

<u><it characterist<="" is="" same="" the="" u=""> Parameter</it></u>	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	_	-	±10	μΑ	V _{GS} =±20V, V _{DS} =0V
Drain-source breakdown voltage	V(BR) DSS	30	_	_	V	ID=1mA, VGS=0V
Zero gate voltage drain current	IDSS	-	_	1	μA	Vds=30V, Vgs=0V
Gate threshold voltage	VGS (th)	1.0	_	2.5	V	V _{DS} =10V, I _D =1mA
		-	59	83		I _D =3.5A, V _{GS} =10V
Static drain-source on-state resistance	RDS (on)	-	93	130	mΩ	I _D =3.5A, V _{GS} =4.5V
resistance		-	107	150		ID=3.5A, VGs=4V
Forward transfer admittance	Y _{fs} *	2.0	-	-	S	I _D =3.5A, V _{DS} =10V
Input capacitance	Ciss	-	140	-	pF	V _{DS} =10V
Output capacitance	Coss	-	45	-	pF	V _{GS} =0V
Reverse transfer capacitance	Crss	-	30	-	pF	f=1MHz
Turn-on delay time	t _{d (on)} *	-	6	-	ns	I _D =1.75A, V _{DD} ≒15V
Rise time	tr *	-	6	-	ns	V _{GS} =10V
Turn-off delay time	td (off) *	-	17	-	ns	R _L =8.57Ω
Fall time	tr *	-	4	-	ns	R _G =10Ω
Total gate charge	Qg *	-	2.5	3.5	nC	V _{DD} ≒15V
Gate-source charge	Q _{gs} *	-	0.8	-	nC	V _{GS} =5V
Gate-drain charge	Q _{gd} *		0.8		nC	ID=3.5A
*Pulsed			0.0			

*Pulsed

•Body diode characteristics (Source-Drain) (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2.>

Forward voltage V _{SD} * – – 1.2 V Is=6.4A, V _{GS} =0V	Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
	Forward voltage		-	-	1.2	V	Is=6.4A, V _{GS} =0V

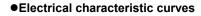
*Pulsed

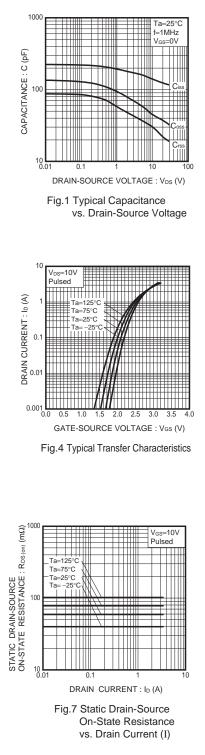
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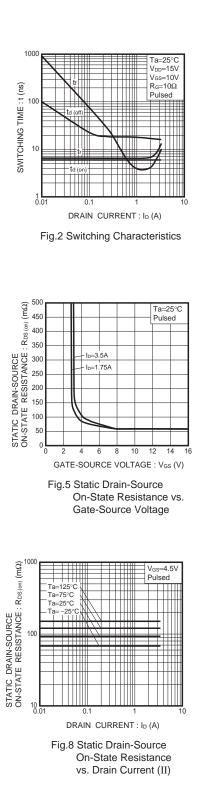
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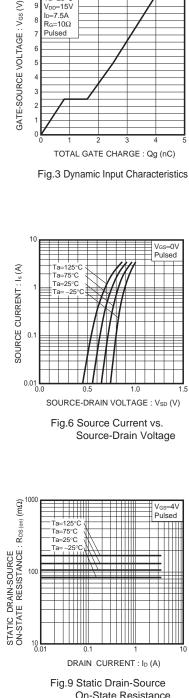
Ta=25°C V_{DD}=15V I_D=7.5A

 $R_{G}=10\Omega$









On-State Resistance vs. Drain Current (III)

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